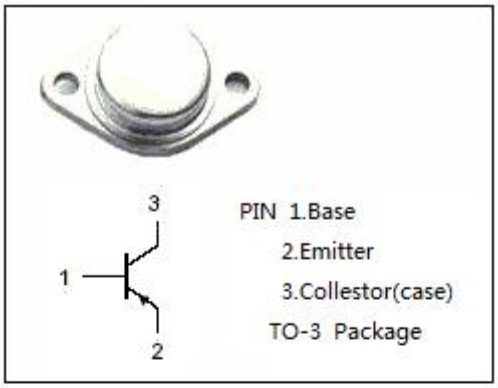
isc Silicon NPN Power Transistor 2N6561



DESCRIPTION

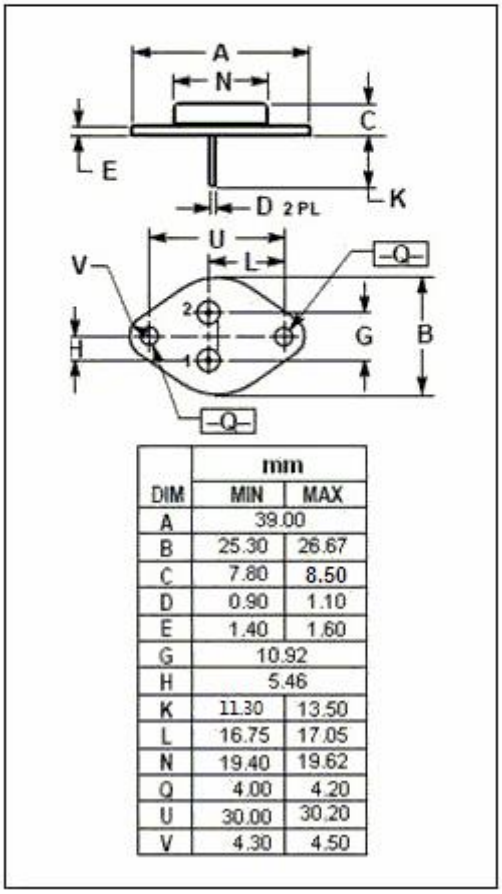
- Collector-Emitter Breakdown Voltage-
  : V_{CEO}=300V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

APPLICATIONS

- Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
P_D	Collector Power Dissipation @ T_C=25℃	220	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C=1mA	300			V
I_{CBO}	Collector-Base Cutoff Current	V_{CB}= 300V			1	mA
I_{EBO}	Emitter-Base Cutoff Current	V_{EB}= 5V			1	mA
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 2A			0.75	V
h_{FE-1}	DC Current Gain	I_C=10A; V_{CE}= 2V	10		50	